Si3473CDV vs. Si3473DV

Description: **P-Channel, 12-V (D-S) MOSFET**
Package: **TSOP-6**
Pin Out: **Identical**

Part Number Replacements: Si3473CDV-T1-E3 or Si3473CDV-T1-GE3 replaces Si3473DV-T1-E3
Si3473CDV-T1-E3 or Si3473CDV-T1-GE3 replaces Si3473DV-T1

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
PARAMETER		**SYMBOL**	**Si3473CDV**	**Si3473DV**	**UNIT**
Drain-Source Voltage		V_{DS}	- 12	- 12	V
Gate-Source Voltage		V_{GS}	± 8	± 8	
Continuous Drain Current	T_A = 25 °C	I_D	- 8	- 7.9	A
	T_A = 70 °C		- 6.5	- 5.7[a]	
Pulsed Drain Current		I_{DM}	- 20	- 20	
Continuous Source Current (MOSFET Diode Conduction)		I_S	- 1.67	- 1.7	
Power Dissipation	T_A = 25 °C	P_D	2.0	2.0	W
	T_A = 70 °C		1.3	1.0[a]	
Operating Junction and Storage Temperature Range		T_J and T_{stg}	- 55 to 150	- 55 to 150	°C
Maximum Junction-to-Ambient		R_{thJA}	62.5	62.5	°C/W

SPECIFICATIONS T_J = 25 °C, unless otherwise noted									
			Si3473CDV			**Si3473DV**			
PARAMETER		**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static									
Gate-Threshold Voltage		$V_{GS(th)}$	- 0.4		- 1	- 0.4		- 1	V
Gate-Body Leakage		I_{GSS}			± 100			± 100	nA
Zero Gate Voltage Drain Current		I_{DSS}			- 1			- 1	µA
On-State Drain Current	V_{GS} = - 4.5 V	$I_{D(on)}$	- 20			- 20			A
Drain-Source On-Resistance	V_{GS} = - 4.5 V	$R_{DS(on)}$		0.016	0.022		0.019	0.023	Ω
	V_{GS} = - 2.5 V			0.021	0.028		0.024	0.029	
	V_{GS} = - 1.8 V			0.026	0.036		0.033	0.041	
Forward Transconductance		g_{fs}		30			28		S
Diode Forward Voltage		V_{SD}		- 0.8	- 1.2		- 0.7	- 1.2	V
Dynamic									
Total Gate Charge		Q_g		26	40		22	33	nC
Gate-Source Charge		Q_{gs}		3.3			3.2		
Gate-Drain Charge		Q_{gd}		7.5			5.8		
Gate Resistance		R_g		4.8			NS		Ω

Note
NS denotes not specified in original specification

a. T_A = 85 °C

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.